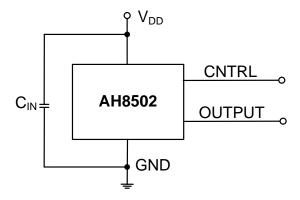


# **Typical Applications Circuit**



Note: 4. C<sub>IN</sub> is for power stabilization and to strengthen the noise immunity, the recommended capacitance is 100nF typical and should be placed as close to the supply pin as possible.

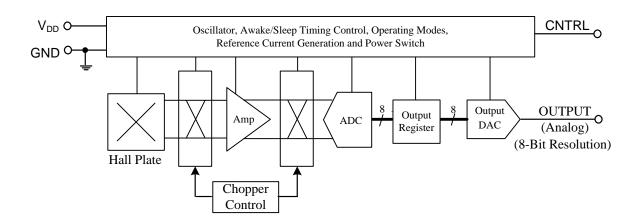
# **Pin Descriptions**

Pin Number	Pin Name	Function
1	OUTPUT	Output Pin
2	NC	No Connection (Note 5)
3	$V_{DD}$	Power Supply Input
4	CNTRL	Device Control Pin: The CNTRL pin allows to select the modes of operation (Micropower Mode, Turbo Mode and External-Drive Mode) and to adjust the sampling rate in External Drive Mode to minimize the power consumption.  When CNTRL = GND or floating, the device operates in default Micropower Mode with 24Hz sampling rate and consumes 13μA typical at 1.8V. The CNTRL pin is internally pulled low.  When CNTRL = V <sub>DD</sub> , the device is on and operates in Turbo Mode with continuous sampling rate of 6.25kHz typical consuming 1.01mA typical at 1.8V.  In External Drive Mode, an external PWM signal can be used to drive the CNTRL pin to adjust the sampling frequency from 24Hz typical up to 7.14kHz typical. If external PWM pulse is used, the minimum pulse width needed on the CNTRL pin to start a sample/conversion is 20μs typical. We recommend using a pulse width of 40μs minimum. The minimum sample and conversion cycle is140μs typical.
5	GND	Ground Pin
6	NC	No Connection (Note 5)
Pad	Pad	The center exposed pad – No connection internally.  The exposed pad can be left open (unconnected) or tied to the GND on the PCB layout.

Note: 5. NC is "No Connection" pin and is not connected internally. This pin can be left open or tied to ground.



# **Functional Block Diagram**





## Absolute Maximum Ratings (Note 6) (@TA = +25°C, unless otherwise specified.)

Symbol	Paramete	Rating	Unit	
$V_{DD}$ and $V_{OUT}$	Supply Voltage and Output Voltage (Note 7)		4	V
$V_{DD\_REV}$ and $V_{OUT\_REV}$	Reverse Supply and Output Voltage	-0.3	V	
I <sub>OUT</sub>	Output Current (Limited by 10kΩ Output Resistor)		V <sub>DD</sub> /10	mA
В	Magnetic Flux Density Withstand		Unlimited	
$P_{D}$	Package Power Dissipation U-DFN2020-6		230	mW
Ts	Storage Temperature Range	-65 to +150	°C	
TJ	Maximum Junction Temperature		+150	°C
ESD HBM	Human Body Model (HMB) ESD Capability		6	kV

Notes:

- 6. Stresses greater than the 'Absolute Maximum Ratings' specified above may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.
- 7. The absolute maximum V<sub>DD</sub> of 4V is a transient stress rating and is not meant as a functional operating condition. It is not recommended to operate the device at the absolute maximum rated conditions for any period of time.

## Recommended Operating Conditions (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Rating	Unit
$V_{DD}$	Supply Voltage	Operating	1.6 to 3.6	V
T <sub>A</sub>	Operating Temperature Range	Operating	-40 to +85	°C

## Electrical Characteristics (Notes 8 & 9) (@T<sub>A</sub> = +25°C, V<sub>DD</sub> = 1.8V, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Supply Curren	Supply Current						
	Average Supply Current in Micropower Mode with Continuous	$V_{OUTPUT} = V_{DD}/2$ , CNTRL = GND, $V_{DD} = 1.8V$ (Note 10)	1	13	20	μΑ	
Sampling Rate of 24Hz (CNTRL = GND Continuously)	$V_{OUTPUT} = V_{DD}/2$ , CNTRL = GND, $V_{DD} = 3.0V$ (Note 10)	1	17	25	μΑ		
Average Supply Current in Turbo  Mode with Continuous Sampling Rate of 6.25Hz (CNTRL = V <sub>DD</sub> Continuously)		$V_{OUTPUT} = V_{DD}/2$ , CNTRL = $V_{DD}$ , $V_{DD} = 1.8V$ (Note 10)	-	1.01	1.3	mA	
	$V_{OUTPUT} = V_{DD}/2$ , CNTRL = GND, $V_{DD} = 3.0V$ (Note 10)	i	1.44	1.8	mA		
DD_7kHz_EXTDRV	Average Supply Current at 7.14kHz Sampling Rate When CNTRL is Externally Driven	$V_{OUTPUT} = V_{DD}/2$ , CNTRL clocking at 7.14kHz, $V_{DD} = 1.8V$ (Note 10)	-	1.16	1.5	mA	
		$V_{OUTPUT} = V_{DD}/2$ , CNTRL clocking at 7.14kHz, $V_{DD} = 3V$ (Note 10)	-	1.65	2.1	mA	

Notes:

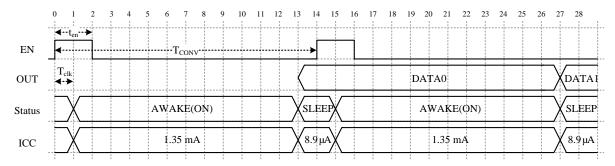
- 8. When power is initially turned on, the operating V<sub>DD</sub> (1.6V to 3.6V) must be applied to guarantee the output sampling. After the supply voltage reaches minimum operating voltage, the output state is valid after t<sub>ON\_INITIAL</sub>..
- 9. Typical data is at  $T_A = +25$ °C,  $V_{DD} = 1.8$ V unless otherwise stated.
- 10. The parameters are not tested in production, they are guaranteed by design, characterization and process control.



# Electrical Characteristics (Cont.) (@T<sub>A</sub> = +25°C, V<sub>DD</sub> = 1.8V, unless otherwise specified.)

#### CNTRL pin timing, conversion rate and I<sub>DD</sub> supply current relationship

## AH8502 CNTRL Pin Driven Externally - External Drive Mode



Status: **AWAKE**: chip processing phase (12\*T<sub>clk</sub>), **SLEEP**: chip retain data

 $T_{clk}$ : internal clock period, typical =  $10 \,\mu s$ 

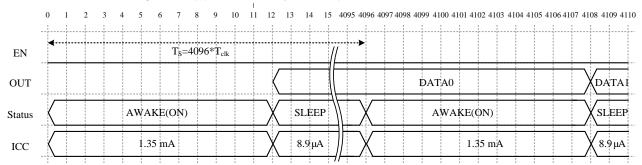
 $t_{en}\!:\!\;$  pulse width of enable signal, minimum=2\*T\_{clk}\!=20\,\mu s (typical)

 $T_{CONV}$ : One sample/conversion cycle =  $14*T_{clk}$ =  $140 \,\mu s$  (typical)

 $I_{DD}$  ( @  $V_{DD} = 1.8V, 25^{\circ}C$ ):

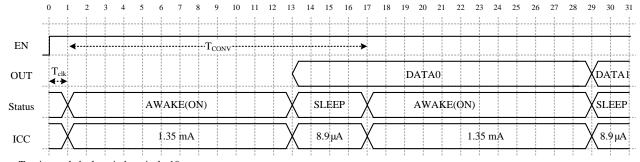
- (1) If CNTRL pin clocked at maximum (~7.14 kHz):  $I_{DD} = 1.35 \text{mA} * 12/14 + 8.93 \,\mu\text{A} * 2/14 \approx 1.16 \text{mA}$
- (2) If CNTRL pin clocked at 24Hz:  $I_{DD} \approx 13 \,\mu A$
- (3) If CNTRL clocking period =T,  $I_{DD}$  = 1.35mA\*120  $\mu$ s/T + 8.93  $\mu$ A\*(T-120  $\mu$ s)/T

### AH8502 CNTRL = GND or Logic Low (0) Continuously - Micropower Mode



Tclk: internal clock period, typical=  $10\,\mu s$   $T_S$ : awake cycle time =  $4096*Tclk \approx 41ms$ 

#### AH8502 CNTRL = V<sub>DD</sub> or Logic High Continuously – Turbo Mode



 $T_{clk}\!\!:$  internal clock period, typical=  $10\,\mu s$ 

 $T_{CONV}$ : One sample/conversion period when ENABLE = Hugh ( $V_{DD}$ ) =  $16*T_{clk}$  =  $160 \,\mu s$ 

 $I_{DD}(\ @\ V_{DD}=1.8V,\,25^{\rm o}C):$ 

 $I_{DD} = 1.35 mA*120\,\mu s/160\,\mu s + 8.93\,\mu A*40\,\mu s/160\,\mu s \approx 1.01 mA~(typical)$ 



# Electrical Characteristics (Cont.) (Notes 11, 12 & 13) (@T<sub>A</sub> = +25°C, V<sub>DD</sub> = 1.8V, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>ON_INITIAL</sub> Initial Power On Time		$V_{DD}=1.8V,T_{A}=+25^{\circ}C,\ C_{IN}=0.1uF,$ $V_{DD}\ rise\ time\ =10\mu s,$ $(Note\ 14)$	-	1	-	ms
ON_INITIAL	illidari owei on tille	$V_{DD}=3V,T_{A}=+25^{\circ}C,C_{IN}=0.1uF,$ $V_{DD}risetime=10\mu s,$ $(Note14)$	-	0.2	-	ms
t <sub>en</sub>	Minimum Pulse Width on CNTRL Pin to Start One Conversion Cycle When Driving CNTRL Pin Externally (See Application Note Section)	$V_{DD} = 1.6V \text{ to } 3.6V, T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$ (Note 14)	-	20	-	μs
T <sub>CONV</sub>	Minimum Period of One Sample/Conversion Cycle	$V_{DD} = 1.6V \text{ to } 3.6V, T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$ (Note 14)	100	140	200	μs
f <sub>MAX</sub>	Maximum Sampling Frequency	$V_{DD} = 1.6V \text{ to } 3.6V, T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C},$ (Note 14)	-	7.14	-	kHz
f_TURBO_MODE	Sampling Frequency in Turbo Mode with CNTRL = V <sub>DD</sub> or Logic High Continuously	CNTRL = High ( $V_{DD}$ ), $V_{DD}$ = 1.6V to 3.6V, $T_A$ = -40°C to +85°C (Note 14)	-	6.25	-	kHz
f_UP_MODE	Sampling Frequency in Micropower Mode with CNTRL = GND or Logic Low Continuously	CNTRL = High ( $V_{DD}$ ), $V_{DD}$ = 1.6V to 3.6V, $T_A$ = -40°C to +85°C (Note 14)	-	24	-	Hz
T_turbo_mode	Awake or Sampling Period in Turbo Mode with CNTRL = $V_{DD}$ or Logic High Continuously	CNTRL = High ( $V_{DD}$ ), $V_{DD}$ = 1.6V to 3.6V, $T_A$ = -40°C to +85°C (Note 14)	-	0.16	-	ms
T_UP_MODE	Awake or Sampling Period in Micropower Mode with CNTRL = GND or Logic Low Continuously.	CNTRL = High ( $V_{DD}$ ), $V_{DD}$ = 1.6V to 3.6V, $T_A$ = -40°C to +85°C (Note 14)	-	41.6	-	ms
V	CNITDI Dia lanut Laur Voltage	V <sub>DD</sub> = 1.8V (Note 13)	0.4	0.5	0.6	V
Vcntrl_low	CNTRL Pin Input Low Voltage	V <sub>DD</sub> = 3.0V (Note 13)	0.8	0.9	1	V
V <sub>CNTRL_HIGH</sub>	CNTRL Pin Input High Voltage	V <sub>DD</sub> = 1.8V (Note 13)	1.2	1.3	1.4	V
- GIVITAL_TILGIT	John Maring Tolkage	$V_{DD} = 3V$ (Note 13)	2.2	2.3	2.4	V
Output Charact	eristics		1			Γ
R <sub>ОИТ</sub>	DC Output Resistance	CNTRL = $V_{DD}$ or GND, $V_{DD} = 1.6V$ to 3.6V, $T_A = -40$ °C to +85°C, (Note 14)	-	10	13	kΩ
Noise DMC	Input Deferred Naise DMC (Note 14)	$C_{IN} = Open, V_{DD} = 1.8V, T_A = +25^{\circ}C,$	-	0.36	-	G
Noise_RMS	Input Referred Noise, RMS (Note 14)	$C_{IN} = Open, V_{DD} = 3.0V, T_A = +25^{\circ}C,$		0.24	-	G
ADC <sub>RES</sub>	Internal ADC and DAC Resolution	(Note 14)	-	8	-	Bit
Vout_res	Output Voltage Resolution	$V_{DD} = 1.6V \text{ to } 3.6V, T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	-	V <sub>DD</sub> /256	-	mV
V <sub>OUTH</sub>	Max. Output Voltage	$V_{DD} = 1.6V \text{ to } 3.6V, T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	-	V <sub>DD</sub> *255/256	-	V
$V_{OUTL}$	Min. Output Voltage	$V_{DD} = 1.6V \text{ to } 3.6V, T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	-	0	-	V

Notes:

- 11. When power is initially turned on, the operating  $V_{DD}$  (1.6V to 3.6V) must be applied to guarantee the output sampling. The output state is valid after  $t_{ON\_INITIAL}$  from the supply voltage reaching the minimum operating voltage.
- 12. Typical data is at  $T_A$  = +25°C,  $V_{DD}$  = 1.8V unless otherwise stated.
- 13. Maximum and minimum parameters values over operating temperature range are not tested in production, they are guaranteed by design, characterization and process control.
- 14. The parameter is not tested in production, they are guaranteed by design, characterization and process control.



## Electrical Characteristics (Cont.) (Note 11, 12 & 13) (@T<sub>A</sub> = +25°C, V<sub>DD</sub> = 1.8V, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Magnetic Char	Magnetic Characteristics						
0	Measurable Magnetic Flux Density	V <sub>DD</sub> = 1.8V, T <sub>A</sub> =+25°C	±370	±430	±505	G	
B <sub>RANGE</sub>	Range	V <sub>DD</sub> = 3V, T <sub>A</sub> =+25°C	±367	±423	±497	G	
0	Carra Basalutian	V <sub>DD</sub> = 1.8V, T <sub>A</sub> =+25°C	2.91	3.35	3.94	G/LSB	
G <sub>RES</sub>	Gauss Resolution	V <sub>DD</sub> = 3V, T <sub>A</sub> =+25°C	2.87	3.30	3.88	G/LSB	
		B = 0.5G, T <sub>A</sub> = +25°C	-	V <sub>DD</sub> / 2	-	V	
V <sub>NULL</sub>	Quiescent Output Voltage with Zero Gauss	V <sub>DD</sub> = 1.8V, T <sub>A</sub> = +25°C	0.882	0.9	0.918	V	
	Gauss	V <sub>DD</sub> = 3V, T <sub>A</sub> = +25°C	1.47	1.5	1.53	V	
		B = 0.5G, V <sub>DD</sub> = 1.8V, T <sub>A</sub> = +25°C	-1%	-	1%	% of V <sub>DD</sub>	
	Quiescent Output Voltage Offset	B = 0.5G, V <sub>DD</sub> = 3V, T <sub>A</sub> = +25°C	-1%	-	1%	% of V <sub>DD</sub>	
Voffset		B = 0.5G, V <sub>DD</sub> = 1.6V to 3.6V,					
		T <sub>A</sub> = -40°C to +85°C	-1.5 -		1.5	% of V <sub>DD</sub>	
		(Note 14)					
$V_{SENS}$	Output Voltage Sensitivity	V <sub>DD</sub> = 1.8V, T <sub>A</sub> = +25°C	1.79	2.1	2.42	mV/G	
VSENS		V <sub>DD</sub> = 3V, T <sub>A</sub> = +25°C	3.02	3.55	4.08		
		V <sub>DD</sub> = 1.8V, T <sub>A</sub> = +25°C	-15	-	15	%	
		V <sub>DD</sub> = 3V, T <sub>A</sub> = +25°C	-15	-	15	%	
V <sub>SENS_ACC</sub>	Sensitivity Accuracy	V <sub>DD</sub> = fixed at any one voltage between					
02/10_/100	,,	1.6V to 3.6V,	-18	_	18	%	
		$T_A = -40$ °C to +85°C	-10		.0	/0	
		(Note 14, Note 15)					
TC_ERR <sub>SENS</sub>	Sensitivity Error over Full Temperature	$V_{DD}$ =fixed, $T_A$ = -40°C to +85°C (Note 14)	-3	-	3	%	
Lin+	Positive Linearity (Span Linearity)	$V_{DD} = 1.8V, T_A = +25^{\circ}C$ (Note 14)	-	99.9	-	%	
LIIIT	Positive Linearity (Span Linearity)	$V_{DD} = 3.0V, T_A = +25^{\circ}C$ (Note 14)	-	99.7	-	%	
Lin	Negative Linearity (Span Linearity)	$V_{DD} = 1.8V, T_A = +25^{\circ}C$ (Note 14)	-	100.1	-	%	
Lin-	Negative Linearity (Span Linearity)	$V_{DD} = 3.0V, T_A = +25^{\circ}C$ (Note 14)	-	100.4	1	%	

Notes:

- 11. When power is initially turned on, the operating  $V_{DD}$  (1.6V to 3.6V) must be applied to guarantee the output sampling. The output state is valid after  $t_{ON\_INITIAL}$  from the supply voltage reaching the minimum operating voltage.
- 12. Typical data is at  $T_A = +25^{\circ}C$ ,  $V_{DD} = 1.8V$  unless otherwise stated.
- 13. Maximum and minimum parameters values over operating temperature range are not tested in production, they are guaranteed by design, characterization and process control.
- 14. The parameter is not tested in production, they are guaranteed by design, characterization and process control.
- 15. This term constitutes of output voltage sensitivity temperature coefficient error and sensitivity accuracy.



## **Application Note**

#### CNTRL Pin - Awake and Sleep Period and Operating Mode Control

The CNTRL pin controls the device operating mode (Micropower, Turbo, External Drive modes) and "Awake" and "Sleep" periods during external drive mode.

When the CNTRL pin is pulled low or GND continuously, the device operates in micropower mode with sampling rate of 24Hz and consumes only 13µA typical at 1.8V. The CNTRL pin is internally pulled low and therefore the default mode is micropower mode if the CNTRL pin is left floating.

When CNTRL is pulled high CNTRL =  $V_{DD}$  (or pulled high) continuously, the device runs in turbo Mode with sampling rate of 6.25kHz and consumes 1.01mA typical at 1.8V. When the CNTRL pin is pulled high continuously, the conversion time  $T_{CONV}$  is 16 clock cycles (160 $\mu$ s typical) and therefore the sampling rate is 6.25kHz.

If the CNTRL pin is driven externally with a PWM signal, the sampling rate can be adjusted from 24Hz to 7.14kHz. A minimum pulse width on CNTRL pin to start a sample/conversion is 20µs typical; we recommend using pulse width of 40µs minimum.

In external drive mode with a PWM signal on the CNTRL pin, the conversion time (signal acquisition, conversion and output update)  $T_{CONV}$  is 14 clock cycles (140µs typical). When the CNTRL goes high, the sample trigger delay is 1 clock pulse (10µs) where supply current remains at 8.93µA typical at  $V_{DD} = 1.8V$ . After the sample trigger delay, the next 12 clock pulse (120µs typical) is 'Awake' period where the typical supply current is 1.35mA at 1.8V supply. The next pulse (10µs) is used to update the output stage and during this time the supply current drops back to 8.93µA typical at 1.8V supply. Therefore, the average supply current of the device depends on the sampling frequency and at the maximum sampling rate of 7.14kHz, it is 1.16mA typical at 1.8V.

The maximum sampling frequency is 7.14kHz when the CNTRL pin is externally driven with a PWM signal.

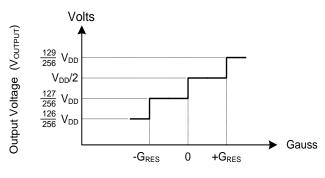
For CNTRL pin clocking period of T, the average current is given by

$$I_{DD} = \frac{1.35mA \times 120\mu s + 8.93\mu A \times (T - 120\mu s)}{T}$$
 (@1.8V)

$$I_{DD} = \frac{I_{DD\_AWAKE} \times 120 \mu s + I_{DD\_SLEEP} \times (T - 120 \mu s)}{T}$$
 (General equation)

#### Quiescent Output Voltage V<sub>NULL</sub> and Offset Voltage

The figure below shows the ideal transfer curve near zero magnetic field (B = 0Gauss). Zero Gauss is the transition point between  $V_{OUTPUT} = V_{DD}*127/128$  and  $V_{OUTPUT} = V_{DD}/2$ . When B is slightly larger than zero, the output is one-half the supply voltage typically. Quiescent output voltage ( $V_{NULL}$ ) is defined as the typical output voltage when B = 0.5Gauss (slightly higher than 0G). Any difference of  $V_{NULL}$  from  $V_{DD}/2$  introduces offset ( $V_{OFSET}$ ).



Magnetic Flux Density (B)

**Transfer Curve Near 0 Gauss** 



## **Application Note (Cont.)**

#### **Sensitivity and Transfer Characteristic**

The device responds to the magnetic flux density perpendicular to the part marking surface. For South pole magnetic flux density increase from  $V_{NULL}$  and for a North magnetic pole field, the output will decrease from  $V_{NULL}$ . The changes in the voltage level up or down are symmetrical to  $V_{NULL}$  and are proportional to the magnetic flux density.

The output voltage change is proportional to the magnitude and polarity of the magnetic field perpendicular to the part marking surface. This proportionality is defined as output voltage sensitivity and is given by

$$V_{SENS} = \frac{(V_{OUT(B\_MAX)} - V_{OUT(B\_MIN)})}{(B_{MAX} - B_{MIN})}$$

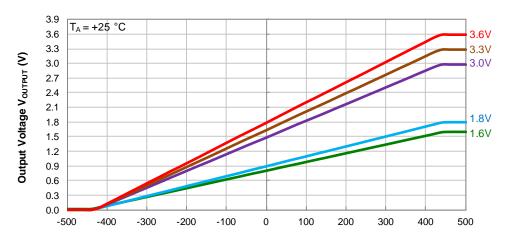
The AH8502 has a measurable magnetic field range of +/-430G and output voltage range of 0V to (255/256)V<sub>DD</sub>. Therefore sensitivity at 1.8V is given by

$$V_{SENS\_1.8V} = \frac{1.8V}{860G} = 2.1mV/G$$

The device has an internal ADC and DAC with resolution of 8-bits. Therefore the measurement resolution is 3.36G/LSB at  $V_{DD} = 1.8V$ . In terms of voltage, the output resolution at 1.8V is 7mV/LSB typical. The device follows the 8-bit step for transfer curve superimposed on the  $V_{SENS}$  above. This difference in theoretical linear value with 8-bit resolution steps produces measurement (quantization) error at each step.

Quantization error (also measurement error) =  $0.5*step = V_{DD}/512$ (output voltage)

Or = Full magnetic range/512 (input magnetic field)



Magnetic Flux Density, B (Gauss)

Transfer Curve - Output Voltage vs. Magnetic Flux Density



# **Application Note (Cont.)**

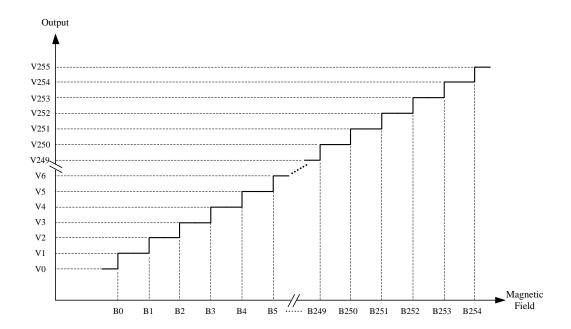
#### **Span Linearity**

Coordinate of transition points ( $V0\sim V255$  and  $B0\sim B254$ ) can be extracted from a transfer curve. Span linearity is defined and based on these coordinate points.

Span linearity is defined as linearity arising from sensitivity differences between the maximum flux density range and half of the range for positive and negative flux density. Referring to the diagram below, north field span linearity LIN- and south field span linearity LIN+ are given by:

$$LIN = \frac{(V0 - V127)/(B0 - B127)}{(V64 - V127)/(B64 - B127)}$$

$$LIN+=\frac{(V254-V127)/(B254-B127)}{(V190-V127)/(B190-B127)}$$

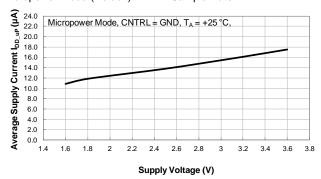




# **Typical Operating Characteristics**

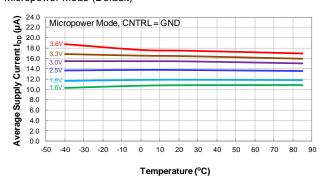
## **Average Supply Current**

Micropower Mode (Default) - 24Hz Sample Rate



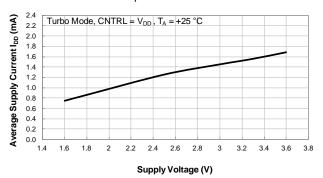
Average Supply Current (CNTRL= GND) vs Supply Voltage

## Micropower Mode (Default)



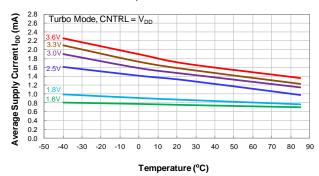
Average Supply Current (CNTRL = GND) vs Temperature

Turbo Mode - 6.25kHz Sample Rate



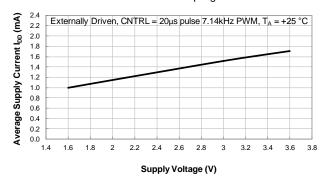
Average Supply Current (CNTRL = V<sub>DD</sub>) vs Supply Voltage

Turbo Mode - 6.25kHz Sample Rate



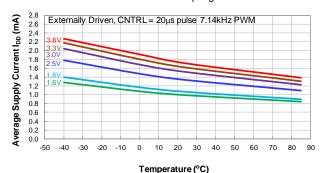
Average Supply Current (CNTRL =  $V_{DD}$ ) vs Temperature

#### External Drive Mode with 7.14kHz Sampling Rate



Average Supply Current (CNTRL = PWM) vs Supply Voltage

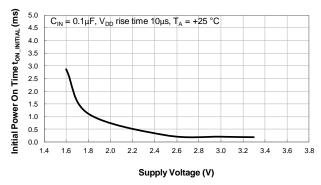
#### External Drive Mode with 7.14kHz Sampling Rate



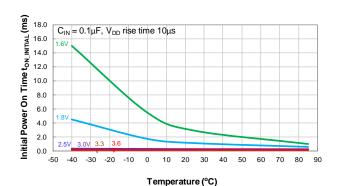
Average Supply Current (CNTRL = PWM) vs Temperature



## **Typical Initial Power On Time**

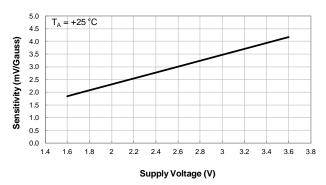


Initial Power On Time vs Supply Voltage

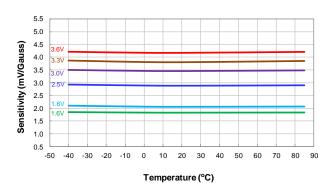


Initial Power On Time vs Temperature

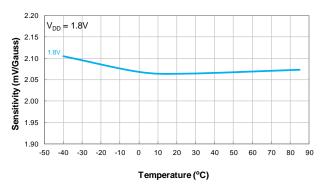
## **Typical Sensitivity**



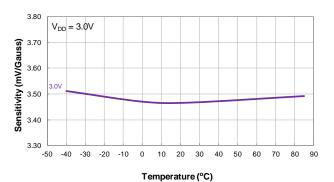
Sensitivity vs Supply Voltage



Sensitivity vs Temperature



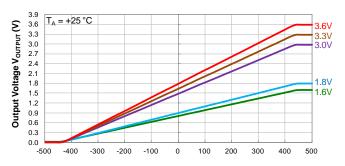
Sensitivity vs Temperature



Sensitivity vs Temperature

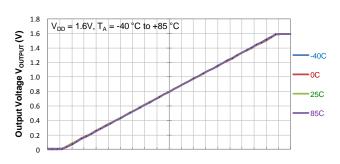


## **Typical Transfer Curves**



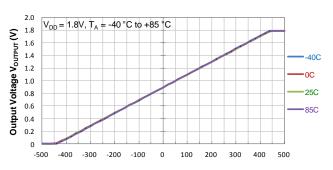
Magnetic Flux Density, B (Gauss)

**Output Voltage vs Magnetic Flux Density** 



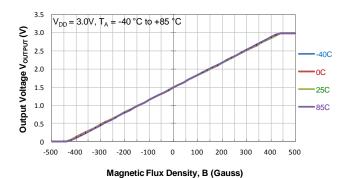
Magnetic Flux Density, B (Gauss)

Output Voltage vs Magntic Flux Density

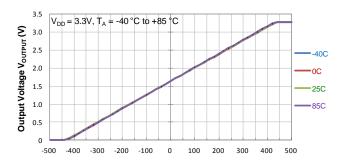


Magnetic Flux Density, B (Gauss)

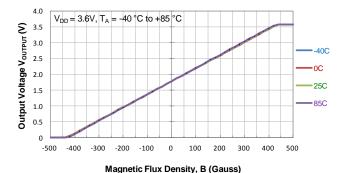
Output Voltage vs Magntic Flux Density



Output Voltage vs Magntic Flux Density



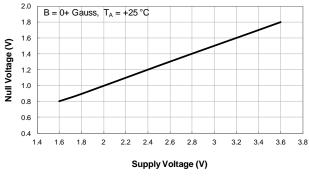
Magnetic Flux Density, B (Gauss)
Output Voltage vs Magntic Flux Density



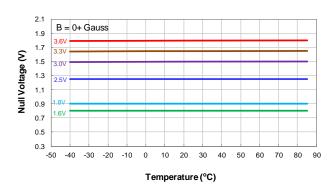
Output Voltage vs Magntic Flux Density



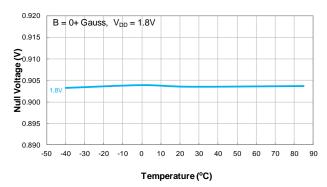
## Typical Null Voltage: Output Voltage at B = 0+ Gauss (Note 16)



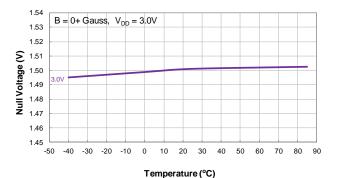
Null Voltage vs Supply Voltage



**Null Voltage vs Temperature** 



**Null Voltage vs Temperature** 



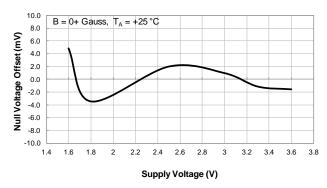
Null Voltage vs Temperature

Note: 16. Null voltage is the voltage with magnetic flux density B = 0G at the sensor. B = 0G is also the transistion point at V<sub>DD</sub>\*127/128 for internal ADC and DAC.

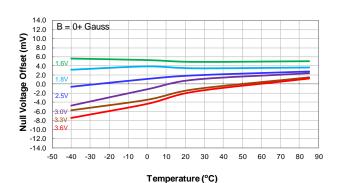
To avoid the transition point fluctuation during measurement of null voltage, B = 0+ Gauss (e.g. 0.5G which is smaller than 1LSB gauss step of 3.125G) is used. See definition of the null voltage in Application Note section.



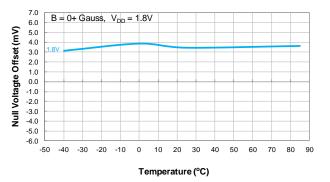
**Typical Null Voltage Offset:** (Output Voltage -  $V_{DD}/2$ ) at B = 0 Gauss (Note 16)



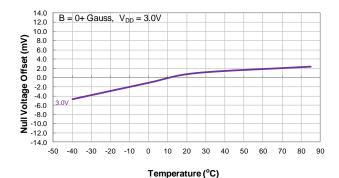
Null Voltage Offset vs Supply Voltage



Null Voltage Offset vs Temperature



Null Voltage Offset vs Temperature



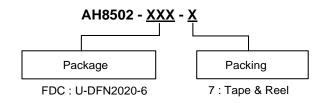
Null Voltage Offset vs Temperature

Note: 16. Null voltage is the voltage with magnetic flux density B = 0G at the sensor. B = 0G is also the transition point at V<sub>DD</sub>\*127/128 for internal ADC and DAC.

To avoid the transition point fluctuation during measurement of null voltage, B = 0+ Gauss (e.g. 0.5G which is smaller than 1LSB gauss step of 3.125G) is used. See definition of the null voltage in Application Note section.



# **Ordering Information**



Part Number	Package	Packaging	7" Tape and Reel	
Fait Number	Code	Packaging	Quantity	Part Number Suffix
AH8502-FDC-7	FDC	U-DFN2020-6	3,000/Tape & Reel	-7

# **Marking Information**

(1) Package Type: U-DFN2020-6

# (Top View)

XX <u>Y W X</u>

 $\underline{XX}$ : Identification Code  $\underline{Y}$ : Year: 0~9

<u>W</u>: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents 52 and 53 week <u>X</u>: Internal Code

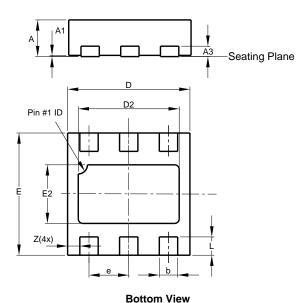
Part Number	Package	Identification Code
AH8502-FDC-7	U-DFN2020-6	KX



# Package Outline Dimensions (All dimensions in mm.)

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

## (1) Package Type: U-DFN2020-6 (Type C)

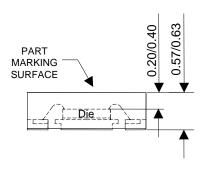


	U-DFN2020-6					
Type C						
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A1	0.00	0.05	0.02			
A3	-	-	0.15			
b	0.25	0.35	0.30			
D	1.95	2.075	2.00			
D2	1.55	1.75	1.65			
E	1.95	2.075	2.0			
E2	0.86	1.06	0.96			
е	-	-	0.65			
L	0.25	0.35	0.30			
Z	-	-	0.20			
All [	Dimens	ions in ı	nm			

# Top view

# 0.86/1.06 Hall Sensor

## Min/Max (in mm)



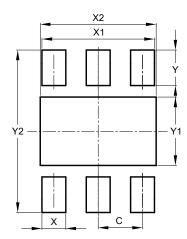
Sensor Location (TBD)



# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

## (1) Package Type: U-DFN2020-6 (Type C)



Dimensions	Value (in mm)
С	0.650
Х	0.350
X1	1.650
X2	1.700
Υ	0.525
Y1	1.010
Y2	2.400



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